AMENDMENTS TO THE CLAIMS

1. (Original) A polishing composition for memory hard disk comprising water and silica particles, wherein the silica particles have a particle size distribution in which a relationship of a particle size (R) and a cumulative volume frequency (V) in a graph of particle size-cumulative volume frequency obtained by plotting a cumulative volume frequency (%) of the silica particles counted from a small particle size side against a particle size (nm) of the silica particles in a range of particle sizes of from 40 to 100 nm satisfy the following formula (1):

$$V \ge 0.5 \times R + 40$$
 (1)

wherein the particle size is determined by observation with a transmission electron microscope (TEM).

- 2. (Original) The polishing composition according to claim 1, wherein the silica particles are colloidal silica particles.
- 3. (Original) The polishing composition according to claim 1, further comprising at least one member selected from the group consisting of acids, salts thereof and oxidizing agents.
- 4. (Original) The polishing composition according to claim 2, further comprising at least one member selected from the group consisting of acids, salts thereof and oxidizing agents.
 - 5. (Original) The polishing composition according to claim 1, wherein pH is from 1 to 4.5.

6. (Original) The polishing composition according to claim 2, wherein pH is from 1 to 4.5.

7. (Original) The polishing composition according to claim 3, wherein pH is from 1 to 4.5.

8. (Original) The polishing composition according to claim 4, wherein pH is from 1 to 4.5.

9. (Withdrawn) A process for reducing surface roughness (TMS-Ra) of a substrate for

memory hard disk comprising the step of polishing a substrate for memory hard disk with the

polishing composition of claim 1.

10. (Withdrawn) A process for reducing surface roughness (TMS-Ra) of a substrate for

memory hard disk comprising the step of polishing a substrate for memory hard disk with the

polishing composition of claim 2.

11. (Withdrawn) A process for reducing surface roughness (TMS-Ra) of a substrate for

memory hard disk comprising the step of polishing a substrate for memory hard disk with the

polishing composition of claim 3.

12. (Withdrawn) A process for reducing surface roughness (TMS-Ra) of a substrate for

memory hard disk comprising the step of polishing a substrate for memory hard disk with the

polishing composition of claim 4.

13. (Withdrawn) A process for reducing surface roughness (TMS-Ra) of a substrate for

memory hard disk comprising the step of polishing a substrate for memory hard disk with the

polishing composition of claim 5.

14. (Withdrawn) A process for reducing surface roughness (TMS-Ra) of a substrate for

memory hard disk comprising the step of polishing a substrate for memory hard disk with the

polishing composition of claim 6.

15. (Withdrawn) A method for manufacturing an Ni-P plated substrate for memory hard disk,

comprising the step of polishing an Ni-P plated substrate for memory hard disk with the polishing

composition of claim 1.

16. (Withdrawn) A method for manufacturing an Ni-P plated substrate for memory hard disk,

comprising the step of polishing an Ni-P plated substrate for memory hard disk with the polishing

composition of claim 2.

17. (Withdrawn) A method for manufacturing an Ni-P plated substrate for memory hard disk,

comprising the step of polishing an Ni-P plated substrate for memory hard disk with the polishing

composition of claim 3.

18. (Withdrawn) A method for manufacturing an Ni-P plated substrate for memory hard disk,

comprising the step of polishing an Ni-P plated substrate for memory hard disk with the polishing

composition of claim 4.

4 of 13

- 19. (Withdrawn) A method for manufacturing an Ni-P plated substrate for memory hard disk, comprising the step of polishing an Ni-P plated substrate for memory hard disk with the polishing composition of claim 5.
- 20. (Withdrawn) A method for manufacturing an Ni-P plated substrate for memory hard disk, comprising the step of polishing an Ni-P plated substrate for memory hard disk with the polishing composition of claim 6.
- 21. (NEW) The polishing composition according to claim 1, wherein the silica particles have a particle size distribution in which the relationship of V and R satisfies the following formula (5):

$$V \ge R + 50 \tag{5}$$

within the range of the particle size of from 40 to 45 nm.